

The 2011 International Meeting for Future of Electron Devices, Kansai (IMFEDK2011) のご案内

日時: 2011年 5月 19日(木) ~ 5月 20日(金) / May 19-20, 2011

場所: 関西大学 100周年記念会館 /

Kansai University Centenary Memorial Hall, Osaka, Japan

URL: <http://www.imfedk.org/>

(Official Language: English)

■ Keynote Speeches

[19th, May]

[1] " **Structure analysis of metal nanoparticle catalysts by environmental transmission electron microscopy** ",

S. Takeda, H. Yoshida and Y. Kuwauchi (Osaka University)

[2] "**Single atom calculation in silicon**",

K. M. Itoh (Keio University)

[20th, May]

[3] "**The Role of High-Doped Source and Drain on Device Performance in Nano-Scale Si-MOSFETs**",

N. Sano (University of Tsukuba)

[4] "**Single-photon detection by SOI MOSFET**",

H. Inokawa (Shizuoka University)

■ Invited Papers for the Special Session

(to be announced soon)

■ Tutorials (*in Japanese*) [19th, May]

[1] "**Current Status of Photovoltaic and Future Technology for Solar Cells**",

「太陽光発電の現状と太陽電池の将来技術」

T. Takamoto (Sharp Corp., Japan)

[2] "**High efficiency quantum dot solar cells: Principles and recent advances**",

Y. Okada (University of Tokyo)